



# STD16NE06L

## N - CHANNEL 60V - 0.07 Ω - 16A - DPAK STripFET™ " POWER MOSFET

PRELIMINARY DATA

TYPE	V <sub>DS</sub>	R <sub>DS(on)</sub>	I <sub>D</sub>
STD16NE06L	60 V	< 0.085 Ω	16 A

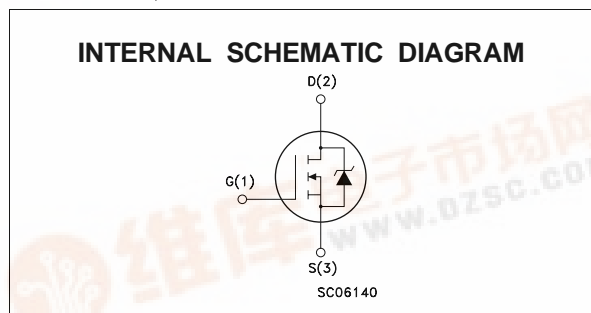
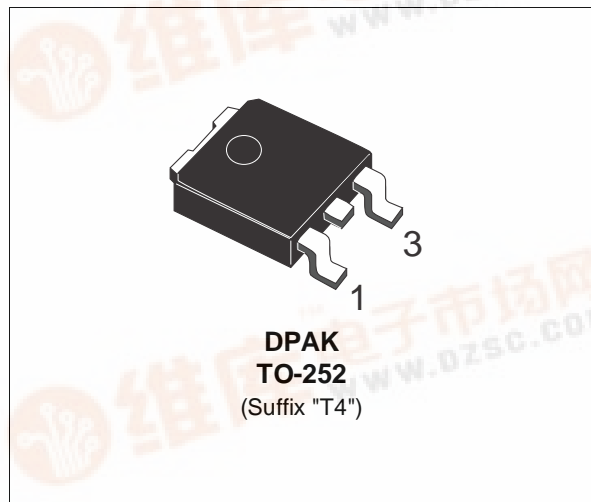
- TYPICAL R<sub>DS(on)</sub> = 0.07 Ω
- EXCEPTIONAL dv/dt CAPABILITY
- 100% AVALANCHE TESTED
- LOW GATE CHARGE 100 °C
- APPLICATION ORIENTED CHARACTERIZATION
- FOR TAPE & REEL AND OTHER PACKAGING OPTIONS CONTACT SALES OFFICES

### DESCRIPTION

This Power Mosfet is the latest development of SGS-THOMSON unique "Single Feature Size™" strip-based process. The resulting transistor shows extremely high packing density for low on-resistance, rugged avalanche characteristics and less critical alignment steps therefore a remarkable manufacturing reproducibility.

### APPLICATIONS

- HIGH CURRENT, HIGH SPEED SWITCHING
- SOLENOID AND RELAY DRIVERS
- MOTOR CONTROL, AUDIO AMPLIFIERS
- DC-DC & DC-AC CONVERTERS



### ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V <sub>DS</sub>	Drain-source Voltage (V <sub>GS</sub> = 0)	60	V
V <sub>DGR</sub>	Drain- gate Voltage (R <sub>GS</sub> = 20 kΩ)	60	V
V <sub>GS</sub>	Gate-source Voltage	± 20	V
I <sub>D</sub>	Drain Current (continuous) at T <sub>c</sub> = 25 °C	16	A
I <sub>D</sub>	Drain Current (continuous) at T <sub>c</sub> = 100 °C	11	A
I <sub>DM</sub> (●)	Drain Current (pulsed)	64	A
P <sub>tot</sub>	Total Dissipation at T <sub>c</sub> = 25 °C	40	W
	Derating Factor	0.3	W/°C
dv/dt	Peak Diode Recovery voltage slope	7	V/ns
T <sub>stg</sub>	Storage Temperature	-65 to 175	°C
T <sub>j</sub>	Max. Operating Junction Temperature	175	°C

(●) Pulse width limited by safe operating area

(1) I<sub>SD</sub> ≤ 16 A, di/dt ≤ 300 A/μs, V<sub>DD</sub> ≤ V<sub>(BR)DSS</sub>, T<sub>j</sub> ≤ T<sub>JMAX</sub>

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### THERMAL DATA

R <sub>thj-case</sub>	Thermal Resistance Junction-case	Max	3.75	°C/W
R <sub>thj-amb</sub>	Thermal Resistance Junction-ambient	Max	100	°C/W
R <sub>thc-sink</sub>	Thermal Resistance Case-sink	Typ	1.5	°C/W
T <sub>l</sub>	Maximum Lead Temperature For Soldering Purpose		275	°C

### AVALANCHE CHARACTERISTICS

Symbol	Parameter	Max Value	Unit
I <sub>AR</sub>	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T <sub>j</sub> max)	16	A
E <sub>AS</sub>	Single Pulse Avalanche Energy (starting T <sub>j</sub> = 25 °C, I <sub>D</sub> = I <sub>AR</sub> , V <sub>DD</sub> = 35 V)	60	mJ

### ELECTRICAL CHARACTERISTICS (T<sub>case</sub> = 25 °C unless otherwise specified)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V <sub>(BR)DSS</sub>	Drain-source Breakdown Voltage	I <sub>D</sub> = 250 μA V <sub>GS</sub> = 0	60			V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current (V <sub>GS</sub> = 0)	V <sub>DS</sub> = Max Rating V <sub>DS</sub> = Max Rating T <sub>c</sub> = 125 °C			1 10	μA μA
I <sub>GSS</sub>	Gate-body Leakage Current (V <sub>DS</sub> = 0)	V <sub>GS</sub> = ± 20 V			± 100	nA

ON (\*)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> I <sub>D</sub> = 250 μA	1	1.7	2.5	V
R <sub>DS(on)</sub>	Static Drain-source On Resistance	V <sub>GS</sub> = 10V I <sub>D</sub> = 8 A V <sub>GS</sub> = 5V I <sub>D</sub> = 8 A		0.07 0.06	0.085 0.07	Ω Ω
I <sub>D(on)</sub>	On State Drain Current	V <sub>DS</sub> > I <sub>D(on)</sub> × R <sub>DS(on)max</sub> V <sub>GS</sub> = 10 V	16			A

### DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g <sub>fs</sub> (*)	Forward Transconductance	V <sub>DS</sub> > I <sub>D(on)</sub> × R <sub>DS(on)max</sub> I <sub>D</sub> = 8 A	5	9		S
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> = 25 V f = 1 MHz V <sub>GS</sub> = 0		800	1100	pF
C <sub>oss</sub>	Output Capacitance			125	170	pF
C <sub>rss</sub>	Reverse Transfer Capacitance			50	70	pF

**ELECTRICAL CHARACTERISTICS** (continued)

SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on Time	$V_{DD} = 30\text{ V}$ $I_D = 10\text{ A}$		20	30	ns
$t_r$	Rise Time	$R_G = 4.7\ \Omega$ $V_{GS} = 5\text{ V}$		45	60	ns
$Q_g$	Total Gate Charge	$V_{DD} = 48\text{ V}$ $I_D = 20\text{ A}$ $V_{GS} = 5\text{ V}$		14	20	nC
$Q_{gs}$	Gate-Source Charge			8		nC
$Q_{gd}$	Gate-Drain Charge			4		nC

SWITCHING OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{r(Voff)}$	Off-voltage Rise Time	$V_{DD} = 48\text{ V}$ $I_D = 20\text{ A}$		10	14	ns
$t_f$	Fall Time	$R_G = 4.7\ \Omega$ $V_{GS} = 5\text{ V}$		25	34	ns
$t_c$	Cross-over Time			42	60	ns

SOURCE DRAIN DIODE

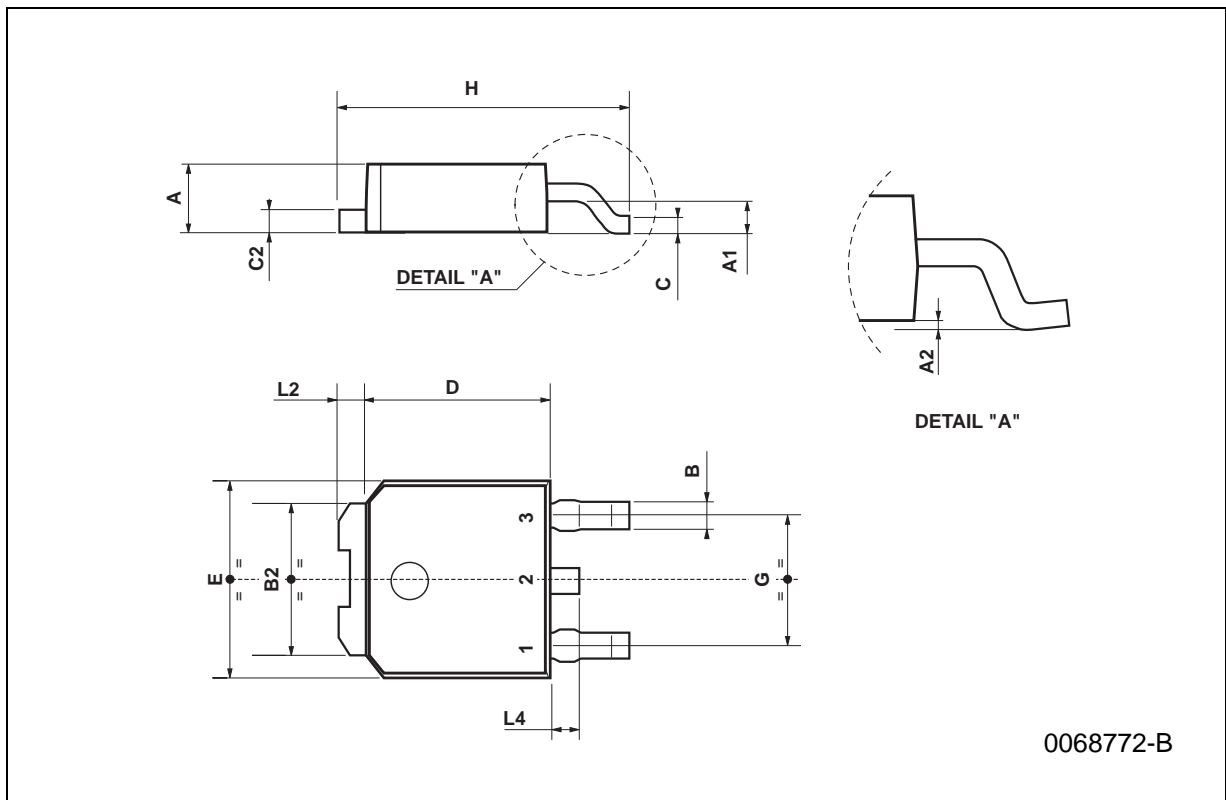
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$I_{SD}$	Source-drain Current				20	A
$I_{SDM}(\bullet)$	Source-drain Current (pulsed)				80	A
$V_{SD} (*)$	Forward On Voltage	$I_{SD} = 16\text{ A}$ $V_{GS} = 0$			1.5	V
$t_{rr}$	Reverse Recovery Time	$I_{SD} = 20\text{ A}$ $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 30\text{ V}$ $T_j = 150\text{ }^\circ\text{C}$		65		ns
$Q_{rr}$	Reverse Recovery Charge			130		$\mu\text{C}$
$I_{RRM}$	Reverse Recovery Current			4		A

(\*) Pulsed: Pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5 %

( $\bullet$ ) Pulse width limited by safe operating area

**TO-252 (DPAK) MECHANICAL DATA**

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	2.2		2.4	0.086		0.094
A1	0.9		1.1	0.035		0.043
A2	0.03		0.23	0.001		0.009
B	0.64		0.9	0.025		0.035
B2	5.2		5.4	0.204		0.212
C	0.45		0.6	0.017		0.023
C2	0.48		0.6	0.019		0.023
D	6		6.2	0.236		0.244
E	6.4		6.6	0.252		0.260
G	4.4		4.6	0.173		0.181
H	9.35		10.1	0.368		0.397
L2		0.8			0.031	
L4	0.6		1	0.023		0.039



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